

FDP8030L/FDB8030L

N-Channel Logic Level PowerTrench® MOSFET

General Description

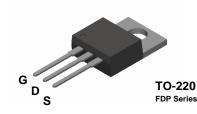
This N-Channel Logic level MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

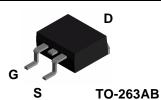
These MOSFETS feature faster switching and lower gate charge than other MOSFETS with comparable $R_{\text{DS(on)}}$ specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

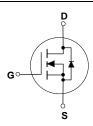
Features

- 80 A, 30 V. $R_{DS(ON)} = 0.0035 \ \Omega \ @ \ V_{GS} = 10 \ V$ $R_{DS(ON)} = 0.0045 \ \Omega \ @ \ V_{GS} = 4.5 \ V$
- Critical DC electrical parameters specified at elevated temperature
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor
- High performance trench technology for extremely low RDS(ON)
- 175°C maximum junction temperature rating





FDB Series



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V _{DSS}	Drain-Source Voltage	30	V
V _{GSS}	Gate-Source Voltage	±20	V
I _D	Drain Current - Continuous (Note 1)	80	Α
	- Pulsed (Note 1)	300]
P _D	Total Power Dissipation @# T _C = 25°C	187	W
	Derate above 25°C	1.25	W°C
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-65 to +175	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	275	°C

Thermal Characteristics

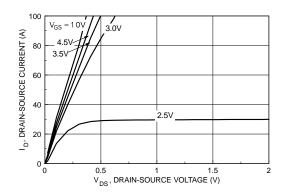
R _θ JC	Thermal Resistance, Junction-to-Case	0.8	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	°C/W

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Drain-Sc	ource Avalanche Ratings (Note	1)				
W _{DSS}	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 20 \text{ V}, \qquad I_D = 80 \text{ A}$			1500	mJ
I _{AR}	Maximum Drain-Source Avalanche Current				80	А
Off Char	acteristics	=				
BV _{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V
ΔBV _{DSS} ΔT _J	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C		23		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, \qquad V_{GS} = 0 \text{ V}$			10	μA
I _{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = 20 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -20 \text{ V}$ $V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)		I			
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	1	1.5	2	V
$\Delta V_{GS(th)}$ $\Delta T_{,J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C		- 5	_	mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$V_{GS} = 10 \text{ V}, \qquad I_D = 80 \text{ A} $ $T_J = 125 ^{\circ}\text{C}$		3.1 4.0	3.5 5.6	mΩ
		$V_{GS} = 4.5 \text{ V}, \qquad I_D = 70 \text{ A}$		3.6	4.5	
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10 \text{ V}, \qquad V_{DS} = 10 \text{ V}$	60			Α
g _{FS}	Forward Transconductance	$V_{DS} = 10 \text{ V}, \qquad I_{D} = 80 \text{ A}$		170		S
Dynamic	Characteristics					
Ciss	Input Capacitance	$V_{DS} = 15 \text{ V}, \qquad V_{GS} = 0 \text{ V},$		10500		pF
Coss	Output Capacitance	f = 1.0 MHz		2700		pF
C _{rss}	Reverse Transfer Capacitance			1650		pF
Switchin	g Characteristics (Note 2)	•	I.			
t _{D(on)}	Turn-On Delay Time	$V_{DD} = 15 \text{ V}, \qquad I_{D} = 50 \text{ A},$		20	35	ns
t _r	Turn-On Rise Time	$V_{GS} = 4.5 \text{ V}, \qquad R_{GEN} = 10 \Omega$		185	225	ns
t _{D (off)}	Turn-Off Delay Time	$R_{GS} = 10 \Omega$		160	200	ns
t _f	Turn-Off Fall Time			200	240	ns
Q _q	Total Gate Charge	V _{DS} = 15 V,		120	170	nC
$\overline{Q_{gs}}$	Gate-Source Charge	$I_D = 80 \text{ A}, V_{GS} = 5 \text{ V}$		27		nC
Q _{gd}	Gate-Drain Charge	1		48		nC
Drain-Se	ource Diode Characteristics	and Maximum Ratings		•		
l _s	Maximum Continuous Drain–Source			80	Α	
I _{SM}	Maximum Pulsed Drain-Source Diode				300	Α
V _{SD}	Drain-Source Diode Forward Voltage			1	1.3	V

Notes:

^{1.} Pulse Test: Pulse Width < $300\mu s$, Duty Cycle < 2.0%

Typical Characteristics



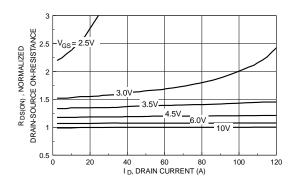
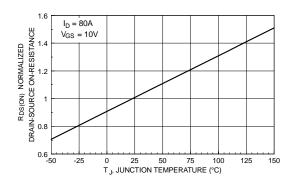


Figure 1. On-Region Characteristics.

Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.



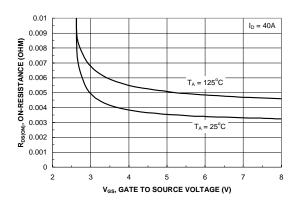
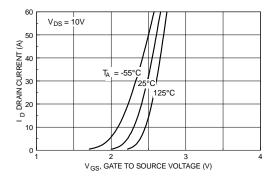


Figure 3. On-Resistance Variation with Temperature.

Figure 4. On-Resistance Variation with Gate-to-Source Voltage.



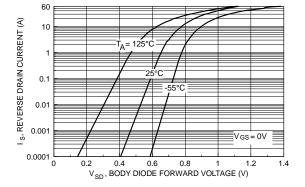


Figure 5. Transfer Characteristics.

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

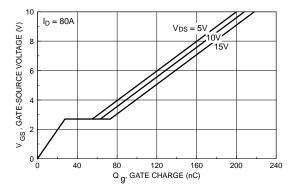


Figure 7. Gate Charge Characteristics.

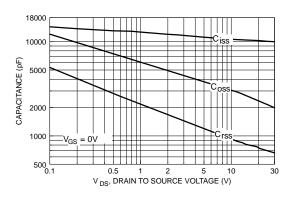


Figure 8. Capacitance Characteristics.

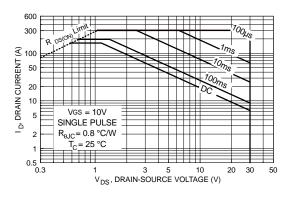


Figure 9. Maximum Safe Operating Area.

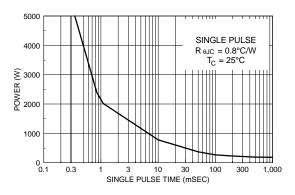


Figure 10. Single Pulse Maximum Power Dissipation.

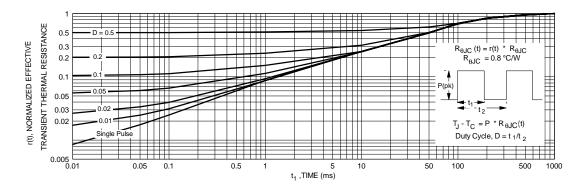
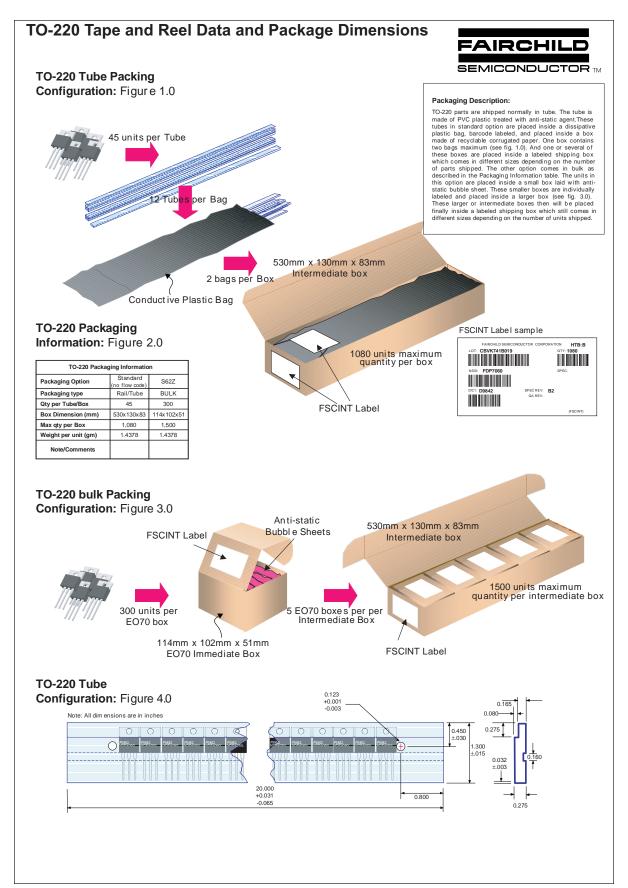


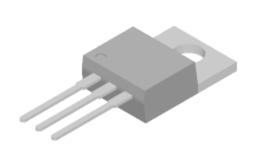
Figure 11. Transient Thermal Response Curve.

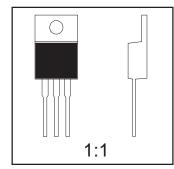
Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.



TO-220 Tape and Reel Data and Package Dimensions, continued

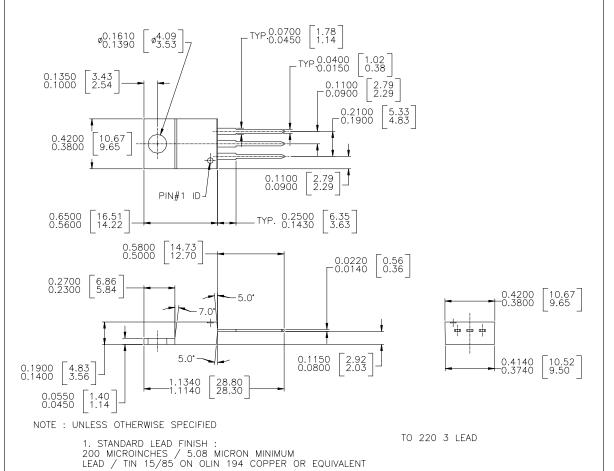
TO-220 (FS PKG Code 37)

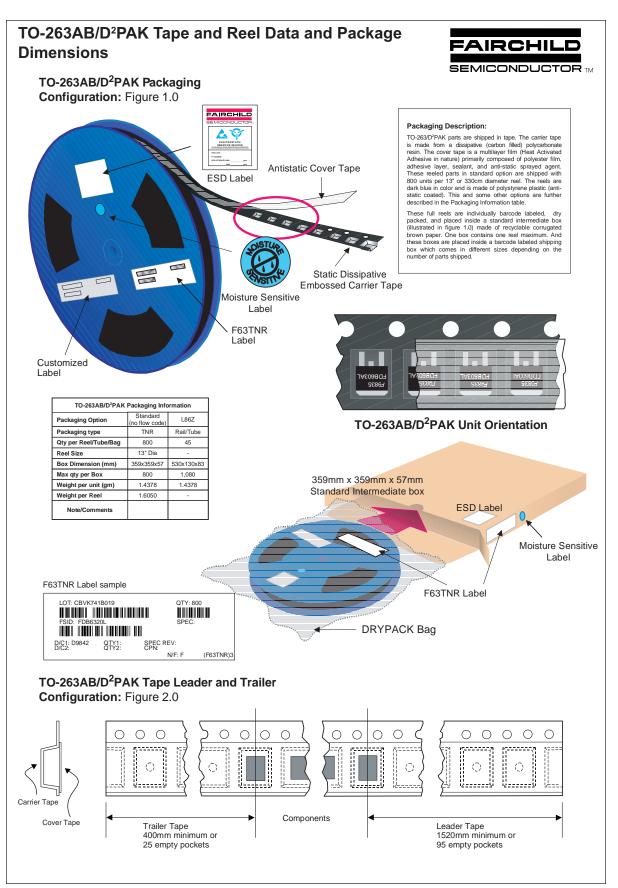




Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

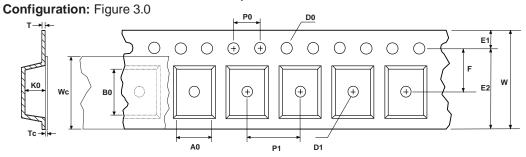
Part Weight per unit (gram): 1.4378





TO-263AB/D²PAK Tape and Reel Data and Package Dimensions, continued

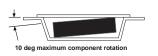
TO-263AB/D²PAK Embossed Carrier Tape



User Direction of Feed

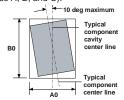
Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
TO263AB/ D ² PAK (24mm)	10.60 +/-0.10	15.80 +/-0.10	24.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	22.25 min	11.50 +/-0.10	16.0 +/-0.1	4.0 +/-0.1	4.90 +/-0.10	0.450 +/-0.150	21.0 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)

Component Rotation

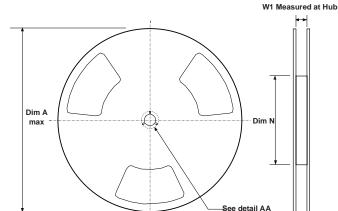


Sketch B (Top View)
Component Rotation

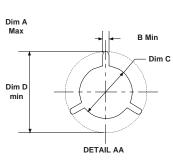


Sketch C (Top View)
Component lateral movement

TO-263AB/D²PAK Reel Configuration: Figure 4.0



13" Diameter Option



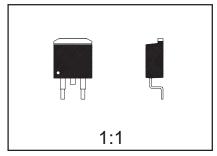
W2 max Measured at Hub

Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
24mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.961 +0.078/-0.000 24.4 +2/0	1.197 30.4	0.941 - 0.1.079 23.9 - 27.4

TO-263AB/D²PAK Tape and Reel Data and Package Dimensions, continued

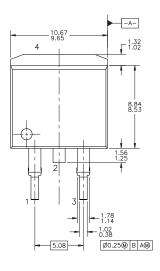
TO-263AB/D²PAK (FS PKG Code 45)

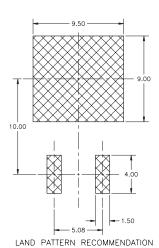


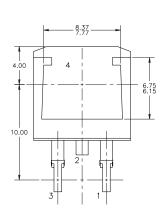


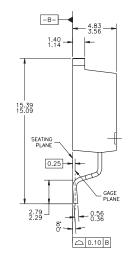
Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 1.4378









- NOTES: UNLESS OTHERWISE SPECIFIED

 A) ALL DIMENSIONS ARE IN MILLIMETERS.
 B) STANDARD LEAD FINISH:
 200 MICROINCHES / 5.08 MICROMETERS MIN.
 LEAD/TIN 15/85 ON OLIN 194 COPPER OR
 EQUIVALENT.
 C) MAXIMUM YERTICAL BURR ON HEATSINK NOT
 TO EXCEED 0.003 INCH / 0.05mm.
 D) NO PACKAGE CHIPS, CRACKS OR SURFACE
 IDENTIFICATION ALLOWED AFTER FORMING.
 E) REFERENCE JEDEC, TO—265, ISSUE C,
 VARIATION AB, DATED 2/92.

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